

The Leader in High Temperature Semiconductor Solutions

CHT-CG50 DATASHEET

Revision: 03.5 Dec. 30, 2014 (Last modified date)

Versatile High-Temperature Clock Generator

General Description

The CHT-CG50 is a versatile High-Temperature crystal clock generator with extended functional capabilities. The chip features a programmable crystal oscillator driver with an enable/disable control signal, an external clock input, a programmable divider chain and a programmable strength three-state output buffer. Using an external crystal, it is intended to provide reliable precision performance throughout the -55 to +225°C temperature range for supply voltages between 3.3V and 5V.

The CHT-CG50 can operate with crystals from 1MHz to 50MHz. The output frequency can be selected by means of a programmable divider, providing division factors of one, two, four and eight. The programmability of the crystal driver allows working with a wide range of crystals. A crystal driver enable pin (/XtalEn) is included for extremely low power applications, as well as an output enable pin (/OE). In applications requiring only a precision divider chain, where an external clock source is already present, the crystal driver may be bypassed by means of inputs ExtClkIn and ExtClkEn.

Features

- Power supply:
 - o 5V +/-10% (1MHZ 50MHz)
 - 3.3V +/-5% (1MHZ 30MHz)
 - Qualified from -55 to +225°C (Tj)
- Two input sources: crystal (1 to 50 MHz), external clock (DC to 50MHz)
- Operation from 32.768kHz crystals
- Programmable frequency divider: fin, fin/2, fin/4 and fin/8
- Programmable crystal driver and output driver strength
- Available in CDIL24 ceramic package.
- Validated at 225°C for 43800 hours (and still on-going)

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- Applications
- Well logging, Automotive, Aeronautics & Aerospace
- Precision timing

Package Configurations¹

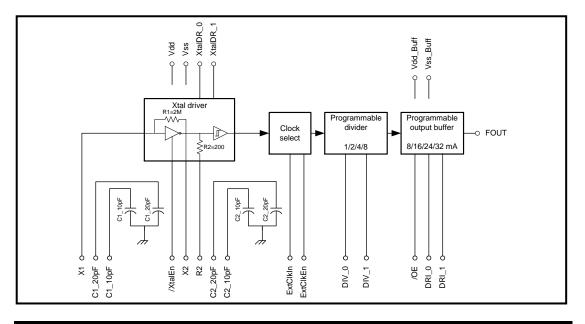
CG50

	DIL24	
Vdd I XtaIDR_1 XtaIDR_0 DRI_1 DRI_0 N.C. DIV_1 DIV_0 ExtClkEn Vss /OE /XtaIEn	0	Vdd_Buff FOUT Vss_Buff Vss ExtClkIn C1_20pF C1_10pF X1 X2 R2 C2_10pF C2_20pF C2_20pF

¹ Other packages available upon request.

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Functional Block Diagram



Pin Description (DIL24)

1	Vdd	Circuit core power supply
		terminal.

а.

2	XtalDR_1	Inputs to set the crystal		
3	XtalDR_0	drive strength.		
-		TRUTH TABLE		
		XtaIDR_1 XtaIDR_0 Strength		
		0 0 Lowest		
		0 1 Low 1 0 High		
		1 1 Highest		
4	DRI 1	Inputs to set the output		
5				
5	DRI_0	buffer strength. TRUTH TABLE		
		DRI_1 DRI_0 Strength		
		0 0 8mA		
		0 1 16mA		
		1 0 24mA		
_		1 1 32mA		
7	DIV_1	Inputs to set the division		
8	DIV 0	factor.		
-		TRUTH TABLE		
		DIV_1 DIV_0 Factor		
		0 0 1		
		0 1 2		
9	ExtClkEn	When driven HIGH, oper-		
3	LAUGIKEII	· · ·		
		ation from the external		
		clock source is selected.		
10	Vss	Circuit core ground termi		
10	V 55	Circuit core ground termi-		
		nal.		
11	/OE	When driven LOW, output		
••	/0L			
		is enabled, When driven		
		HIGH, output is at high		
		impedance.		
		in possiloo.		
12	/XtalEn	When driven LOW, the		
		crystal oscillator is ena-		

bled. When driven HIGH, the crystal oscillator is stopped.

- 13C2_20pFBuilt-in capacitors with a14C2_10pFcommon terminal connected to Vss.
- **15 R2** Terminal of a 200Ω resistor. The other terminal of this resistor is connected to X2.
- 16 X2 Output of crystal driver
- **17 X1** Input of crystal driver
- 18 C1_10pF Built-in capacitors with a
 19 C1_20pF common terminal connected to Vss.
- 20 ExtClkIn Input for an external clock source.
- 21 Vss Circuit core ground terminal.
- 22 Vss_Buff Output buffer ground terminal.
- 23 FOUT Output signal.
- 24 Vdd_Buff Output buffer power supply terminal.



(Last modified date)

Absolute Maximum Ratings

Operating Conditions Supply Voltage V_{DD} to GND

Supply Voltage V_{DD} to GNE Junction temperature

3.3V to 5V -55°C to +225°C

ESD Rating Human Body Model

Class0 (<250V)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Frequent or extended exposure to absolute maximum rating conditions or above may affect device reliability.

Electrical Characteristics

Unless otherwise stated: $V_{DD}=5V$, <u>T_j=150°C</u>. **Bold underlined** values indicate values over the whole temperature range (-55°C < T j < +225°C).

Parameter	Condition	Min	Тур	Max	Units
Supply voltage		3.13		5.5	V
V _{DD}					
	V_{DD} = 3.3V, F_{IN} = 1MHz Output disabled (/OE: HIGH)		0.1	<u>0.16</u>	
	$V_{DD} = 3.3V$, $F_{IN} = 1$ MHz				
	Output enabled (/OE: LOW)		0.25	0.32	
	$C_L = 22pF$				
	$V_{DD} = 3.3V, F_{IN} = 27MHz$		0.64	0.67	
	Output disabled (/OE: HIGH)	_			-
	V_{DD} = 3.3V, F_{IN} = 27MHz Output enabled (/OE: LOW)		4.73	4.79	
	$C_L = 22pF$			<u></u>	
	$V_{DD} = 5V, F_{IN} = 1MHz$		0.41	0.69	
	Output disabled (/OE: HIGH)		0.41	0.03	_
	$V_{DD} = 5V$, $F_{IN} = 1MHz$		0.05		
Current consumption ¹	Output enabled (/OE: LOW) $C_L = 22pF$		0.65	<u>0.94</u>	
Idd	$V_{DD} = 5V$, $F_{IN} = 27MHz$	-			mA
	Output disabled (/OE: HIGH)		1.33	<u>1.40</u>	
	$V_{DD} = 5V, F_{IN} = 27MHz$				
	Output enabled (/OE: LOW)		7.91	<u>8.06</u>	
	$C_L = 22pF$				
	$V_{DD} = 5V, F_{IN} = 35MHz$ Output disabled (/OE: HIGH)		1.91	<u>1.96</u>	
	$V_{DD} = 5V, F_{IN} = 35MHz$				
	Output enabled (/OE: LOW)		10.61	10.74	
	$C_L = 22pF$				
	$V_{DD} = 5V, F_{IN} = 50MHz$		2.15	2.35	
	Output disabled (/OE: HIGH) $V_{DD} = 5V, F_{IN} = 50MHz$	-			
	$V_{DD} = 5V, F_{IN} = 5000HZ$ Output enabled (/OE: LOW)		14.26	14.37	
	$C_L = 22pF$		11.20	<u></u>	
Minimum HIGH level output					
voltage	$R_{LOAD} = 600\Omega$	<u>4.67</u>			V
V _{он} Maximum LOW level output		+			
voltage	$R_{LOAD} = 600\Omega$			0.30	V
V _{oL}					
Minimum HIGH level input					
voltage		<u>3.15</u>			V
V _{IH} Maximum LOW level input					<u> </u>
voltage				1.35	V
V _{IL}		1			
Internal capacitors					
Initial accuracy			17		%
Temperature drift	$\Delta T = 225^{\circ}C - 25^{\circ}C$		0.6		%
TC1	$C(T) = C(T_0) [1+TC1.(T-T_0)+TC2.(T-T_0)+TC2.(T-T_0)]$		0.023		$10^{-3}/K$
TC2	$TC2.(T-T_0)^2$]		0.013		10 ⁻⁶ /K ²

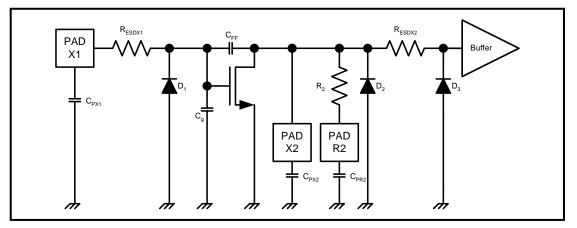
¹ The given value includes the consumption due to the load. Current consumption due to a capacitive load must be computed according to $I_{LOAD} = C_L V_{DD}.f.$

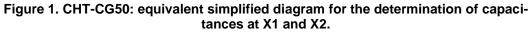


AC Electrical Characteristics

Unless otherwise stated: V_{DD} =5V, T_i =150°C. Bold underlined values indicate values over the whole temperature range ($-55^{\circ}C < T j < +225^{\circ}C$).

Parameter	Condition	Min	Тур	Max	Units	
Frequency range F _{IN}		1		50	MHz	
	$F_{IN}=1MHz, V_{DD}=5V$		52/48	<u>53/47</u>		
Duty cycle @ 50% V _{DD}	$F_{IN}=27MHz, V_{DD}=5V$		45/55	44/56	%	
	$F_{IN}=35MHz, V_{DD}=5V$		44/56	<u>44/56</u>	70	
	F_{IN} =50MHz, V_{DD} = 5V		42/58	<u>42/58</u>		
Output rise time ³ 10% to 90% Vpp	Vdd = 5V, Z_{LOAD} = 1M Ω // 22pF		<u>3.0</u>		20	
t _r	Vdd = 5V, Z_{LOAD} = 600 Ω // 15pF		2.5		ns	
Output fall time ⁴ 10% to 90% Vpp	Vdd = 5V, Z_{LOAD} = 1M Ω // 22pF		<u>2.5</u>		ns	
t _f	Vdd = 5V, Z_{LOAD} = 600 Ω // 15pF		2.1		115	
Oscillation established after Vdd goes high ⁴ t _{power-on}	V_{DD} from 0 to 5V		1.2 <u>3.2</u>		ms	
Oscillation established after /XtalEn goes LOW ⁵ t _{start-up}	V _{DD} = 5V /XtaIEn from LOW to HIGH		0.6 <u>1.4</u>		ms	
Equivalent capacitance at	Passive⁵. Freq= 1MHz	<u>0.89</u>		<u>0.93</u>		
driver input (X1) C _{X1}	Active ⁶ . Freq= 1MHz	<u>1.56</u>		<u>2.81</u>	pF	
Equivalent capacitance at driver output (X2) C _{X2}	Freq= 1MHz	<u>0.54</u>		<u>0.91</u>	pF	
Equivalent capacitance at limiting resistor (R2) C_{R2}	Freq= 1MHz	<u>0.27</u>		<u>0.35</u>	pF	





Duty cycle is measured with a unitary division factor and Z_{LOAD} = 1050 Ω // 22pF. 2

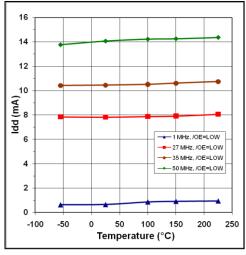
Depends on used crystal and R2 value.

³ Depends on load conditions and DRI_0, DRI_1 settings. ⁴ Depends on used crystal and XtaIDR_0, XtaIDR_1 settings.

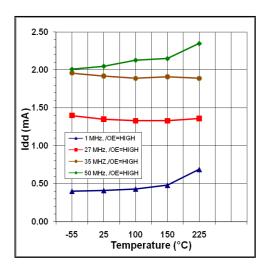
⁵ Considers all capacitances but without taking into account Miller effect on C_{FF} (see **Figure 1**).

⁶ Considers all capacitances including Miller effect on C_{FF} (see **Figure 1**).

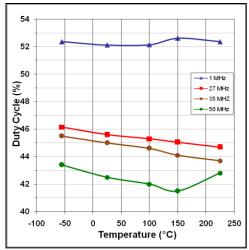
Typical Performance Characteristics



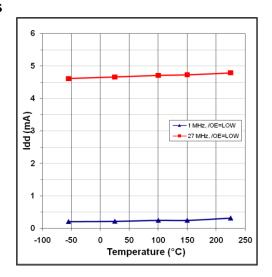
 $\label{eq:current} \begin{array}{l} \text{Current consumption, } V_{\text{DD}} = 5V, \, /\text{OE} = \text{LOW}, \\ C_{\text{L}} = 22pF \end{array}$



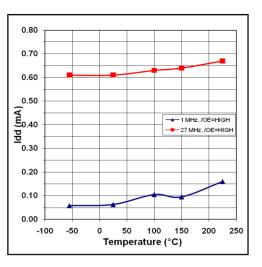
Current consumption, $V_{DD} = 5V$, /OE = HIGH



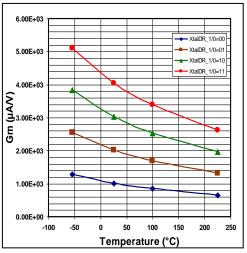




Current consumption, V_{DD} = 3.3V, /OE = LOW, C_L = 22pF



Current consumption, $V_{DD} = 3.3V$, /OE = HIGH



Transconductance of crystal driver, $V_{DD} = 5V$



(Last modified date)

Circuit Functionality

Operating conditions

The CHT-CG-050 is qualified for supply voltages ranging from 3.3V up to 5.5V.

The operating temperature range extends from -55°C to +225°C.

Crystal driver

XtaIDR_0 and **XtaIDR_1** allow the crystal driver to change its strength to be able to oscillate with a wide range of crystals, under any supply (3.3V to 5V) and temperature (up to 225°C) condition.

The presence of integrated passive components offers a great versatility to the final user. Highly temperature-stable capacitors allow for a nearly-constant crystal load along the whole temperature range. Internal passive components can be bypassed or tied to ground if needed.

/XtalEn enables or disables the crystal oscillator to operate, allowing the CHT-CG-050 to be embedded into power-optimized high-temperature applications.

Clock source selector

By means of **ExtClkEn** and **ExtClkIn**, the CHT-CG-050 is able to operate either from its internal crystal oscillator or from an external clock source.

Frequency divider

Four division factors (1, 2, 4 and 8) can be selected depending on the levels at the control lines **DIV_0** and **DIV_1**.

Output buffer

A programmable-strength output buffer, controlled by **DRI_0** and **DRI_1**, enables the CHT-CG-050 to drive a large range of output loads, improving the output signal integrity. The four possible output strengths are 8mA, 16mA, 24mA and 32mA.

The output buffer has supply terminals independent from the rest of the circuit, allowing the system designer to properly decouple them in noise-sensitive application.

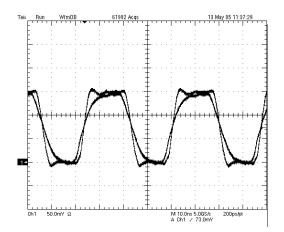


Figure 2. Effect of DRI_0 and DRI_1 on the output signal.

Figure 2 shows the superposition of the output signal when **DRI_0**, **DRI_1** = LOW and **DRI_1** is then set to HIGH, V_{DD} =3.3V, T=235°C, Freq = 27MHz. As a result, the signal integrity is improved.

Packaging options

As mentioned above, the layout of the CHT-CG-050 allows for a very high level of flexibility for the system designer. Several packaging configurations are possible, from 8-pin to 24-pin standard carriers.

At the packaging stage, many functional features can be enabled or safely disabled in order to optimize the form factor according to the final user needs.

Typical application

The CHT-CG-050 offers the final user several possible configurations depending upon the characteristics of the target application.

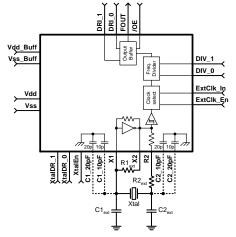


Figure 3. Full configuration.

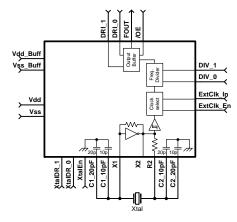


Figure 4. Minimal configuration.

Dashed lines in Figure 3 indicate optional connections. Figure 4 shows the minimal possible configuration with no external components. Any configuration in between those of Figure 3 and Figure 4 can be obtained by properly bypassing or tying to ground the corresponding internal component.

Any programmable feature can be changed on-the-fly, allowing the CHT-CG-050 to accommodate to new operating conditions in smart or adaptive applications.

Output impedance matching

The CHT-CG50 is able to provide an output signal with very short transition times (<10ns). During this transition periods, the

output signal must be seen as a signal with a frequency above 100MHz. Under this assumption, PCB traces or cables connected to the output represent inductors or even transmission lines.

Signal integrity good practices must be considered when driving PCB traces or cables with the CHT-CG50 output. PCB traces or cables can induce ringing and even reflections back to the output buffer. Too much reflection onto the output buffer may cause overshoots and undershoots on the CHT-CG50 terminals exceeding the Absolute Maximum Ratings of the device leading to permanent damage.

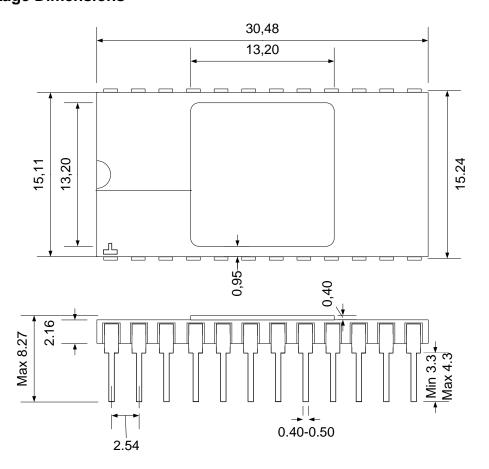
To reduce or avoid ringing or signal reflection. impedance matching considerations must be taken into account. To do so. adapt the CHT-CG50 output drives strength (DRI_0 and DRI_1) to the final application load conditions, place capacitive loads as close as possible of the CHT-CG50 output, keep traces and cables as short as possible and, when driving long traces or cables cannot be avoided, place a resistor in series with the output as close to it as possible in order to match the trace or cable impedance. This resistor, general-Iv in the range from 10Ω to 100Ω must be experimentally determined given the final application load conditions.

Ordening Defenses	
Ordering Reference Package Temperature Range Markin	g
CHT-CG50-DIL24-T Ceramic DIL24 -55°C to +225°C CHT-CG	50

Ordering Information



Package Dimensions



Drawing CDIL24 (mm +/-10%)

Contact & Ordering

CISSOID S.A.

Headquarters and contact EMEA:	CISSOID S.A. – Rue Francqui, 3 – 1435 Mont Saint Guibert - Belgium T : +32 10 48 92 10 - F: +32 10 88 98 75 Email: <u>sales@cissoid.com</u>
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